

ABSTRACT OF THE DISCLOSURE

A nonvolatile memory device has a plurality of nonvolatile memory cells in which a memory gate electrode is formed over a first semiconductor region with a gate insulating film and a gate nitride film interposed therebetween. First and second switch gate electrodes, and first and second signal electrodes used as source/drain electrodes are formed on both sides of the memory gate electrode. Electrons are injected into the gate nitride film from the source side to store information in the memory cells. The memory gate electrode and the switch gate electrodes extend in the same direction. The application of a high electric field to a memory cell which is not selected for writing can be avoided owing to the switch gate electrodes being held in a cut-off state.